

N-Channel Silicon MOSFET

SANYO

2SK1475

Ultrahigh-Speed Switching Applications

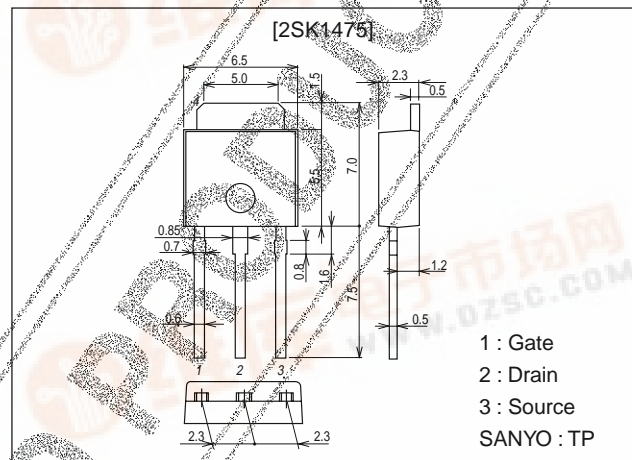
Features

- Low ON resistance.
- Ultrahigh-speed switching.
- Low-voltage drive.

Package Dimensions

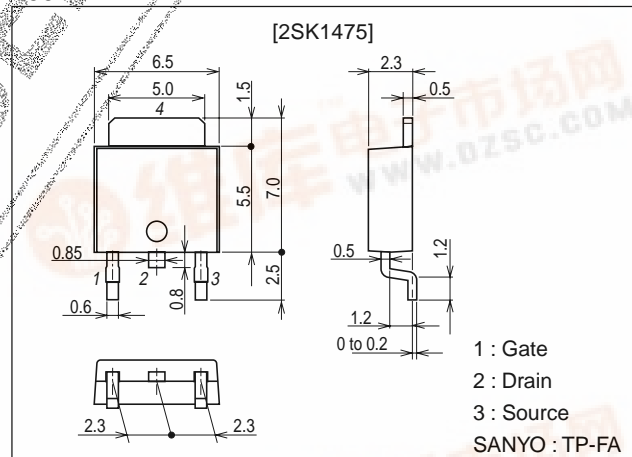
unit:mm

2083B



unit:mm

2092B



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Specifications

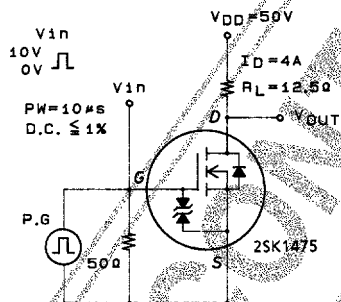
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		100	V
Gate-to-Source Voltage	V_{GSS}		±15	V
Drain Current (DC)	I_D		8	A
Drain Current (pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	32	A
Allowable Power Dissipation	P_D	$T_c = 25^\circ C$	30	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

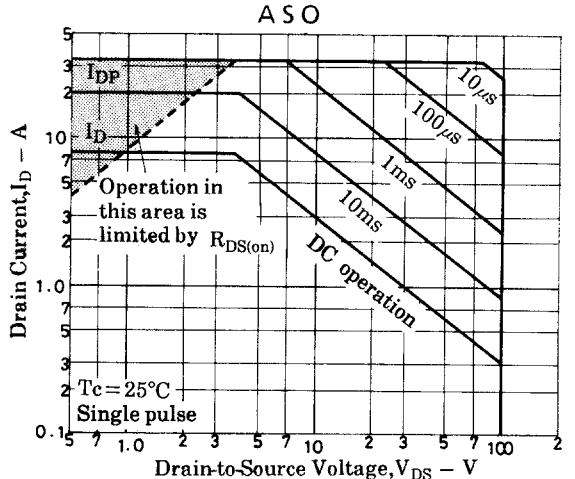
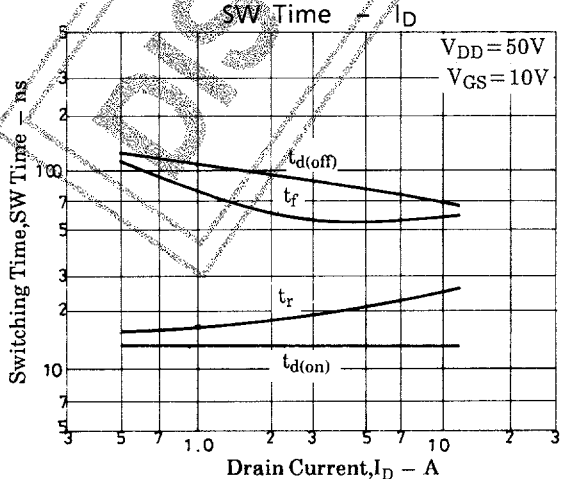
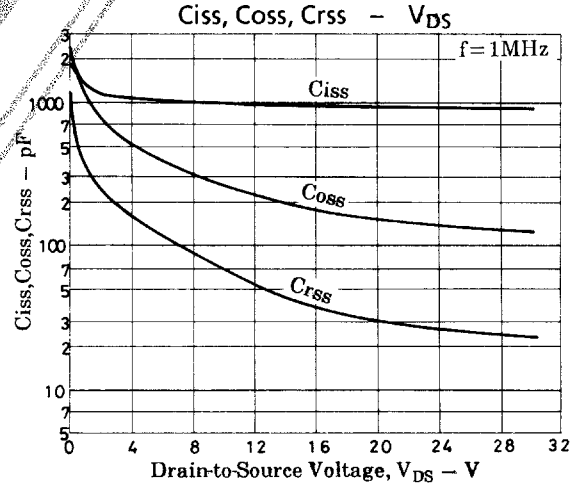
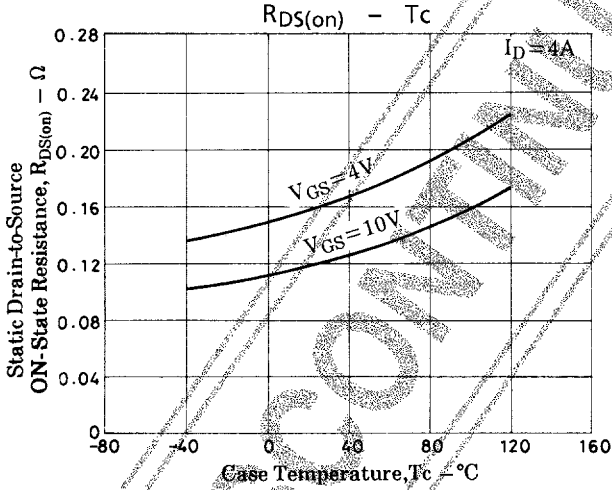
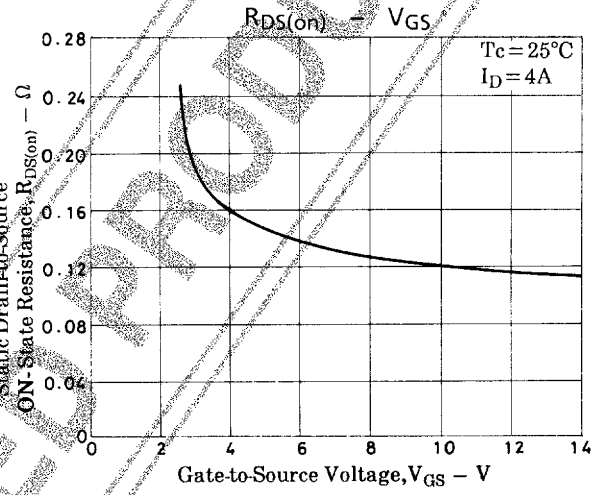
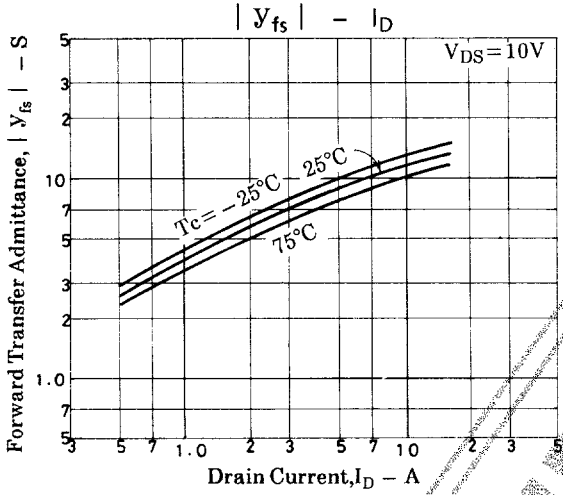
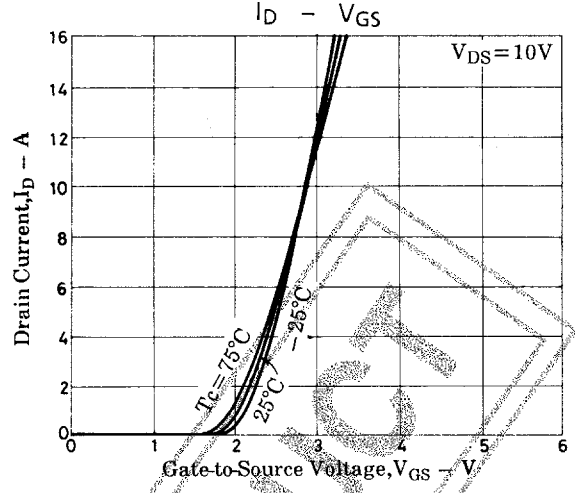
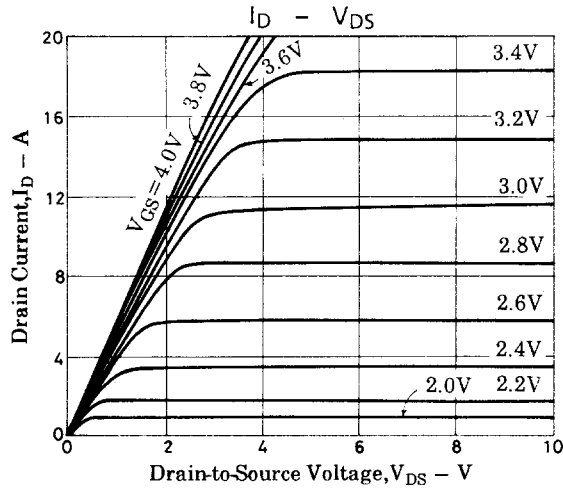
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1mA$, $V_{GS} = 0$	100			V
Gate-to-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A$, $V_{DS} = 0$	±15			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V$, $V_{GS} = 0$			100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V$, $V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V$, $I_D = 1mA$	1.0		2.0	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 10V$, $I_D = 4A$	5	8		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = 4A$, $V_{GS} = 10V$		0.12	0.16	Ω
	$R_{DS(on)2}$	$I_D = 4A$, $V_{GS} = 4V$		0.16	0.22	Ω
Input Capacitance	C_{iss}	$V_{DS} = 20V$, $f = 1MHz$		950		pF
Output Capacitance	C_{oss}	$V_{DS} = 20V$, $f = 1MHz$		150		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 20V$, $f = 1MHz$		30		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		13		ns
Rise Time	t_r	See specified Test Circuit		20		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		85		ns
Fall Time	t_f	See specified Test Circuit		55		ns
Diode Forward Voltage	V_{SD}	$I_S = 8A$, $V_{GS} = 0$	1.0	1.5		V

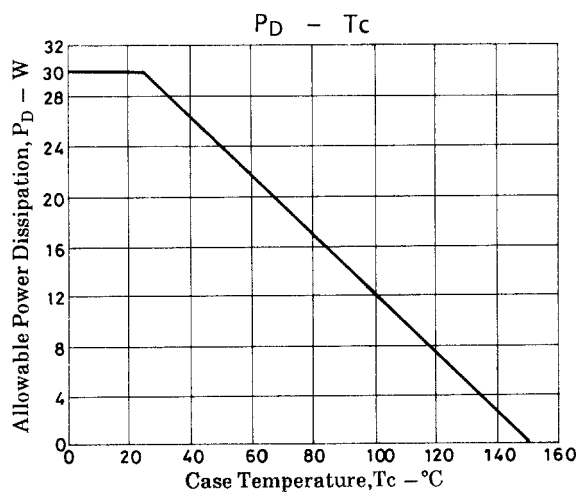
Switching Time Test Circuit



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